

/ Descriptions

WR0553I ММ Ё SQS æ Ñ ç s ll 1 Silicon PNP transistor in a TO-220F Plastic Package.

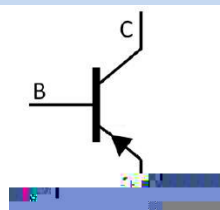
/ Features

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High V_{CEO} , large P_C .

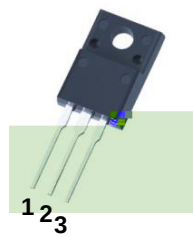
/ Applications

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Power amplifier, TV vertical deflection output.

/ Equivalent Circuit



/ Pinning



PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

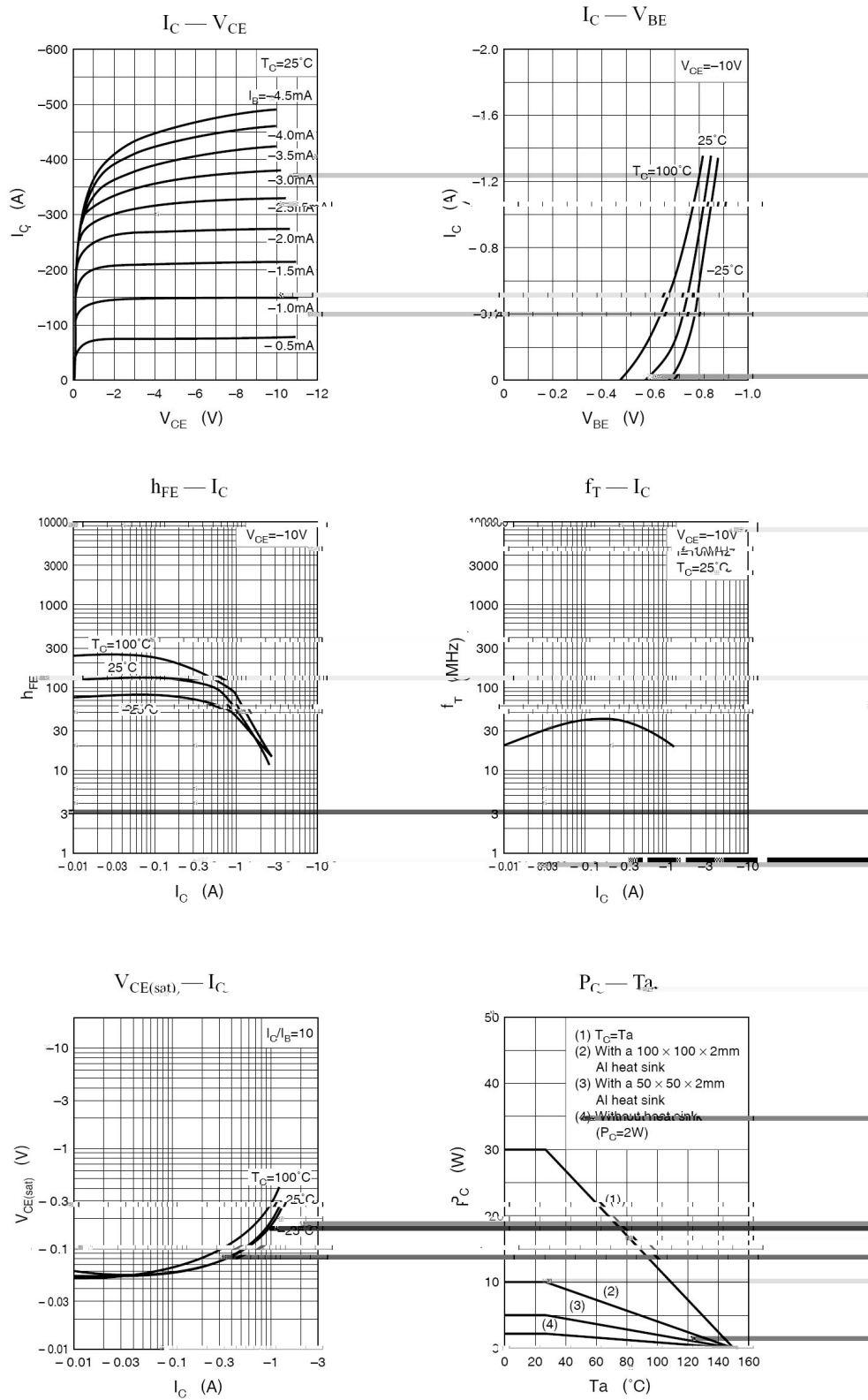
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	Q	P
h_{FE} Range	60 140	100 240

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-200	V
Collector to Emitter Voltage	V_{CEO}	-150	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current - Continuous	I_C	-2.0	A
Collector Current – Continuous(Pulse)	I_{CP}	-3.0	A
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	$P_C(T_c=25^\circ C)$	30	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -500\mu A, I_E = 0$	-200			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -5.0mA, I_B = 0$	-150			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E = -5.0mA, I_B = 0$	-6.0			V

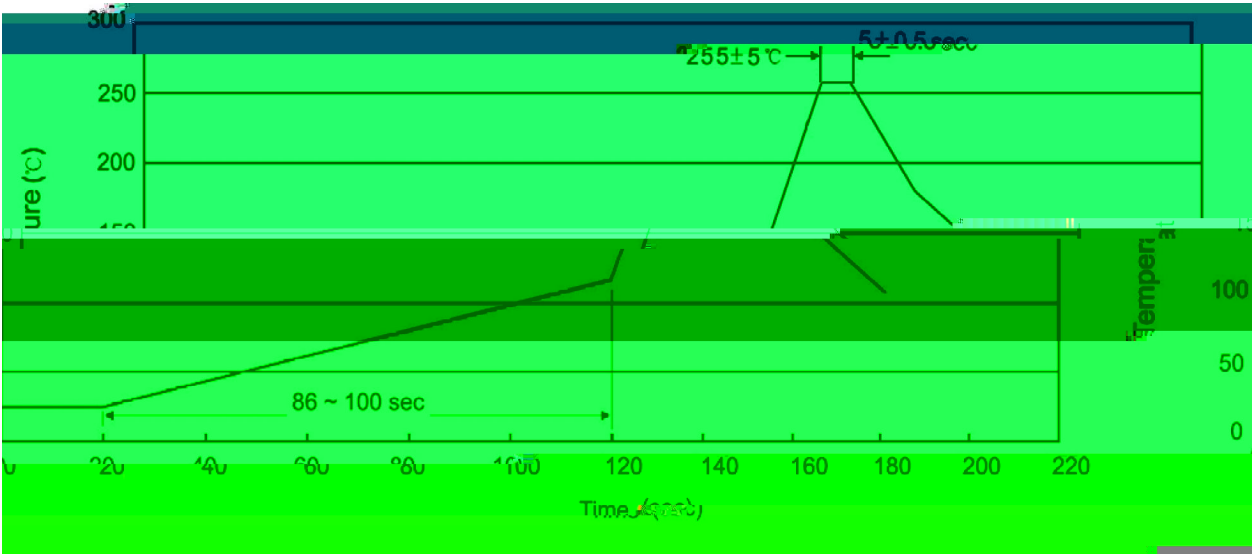
/ Electrical Characteristic Curve



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Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



- 说明

 1. 预加热: 25~150℃, 时间: 60~90sec;
 2. 峰值温度: 255±5℃, 持续时间: 5±0.5sec;
 3. 冷却速度: 2~10℃/sec.
- Note:

 - 1.Preheating:25~150℃, Time:60~90sec.
 - 2.Peak Temp.:255±5℃, Duration:5±0.5sec.
 3. Cooling Speed: 2~10℃/sec.

/ Resistance to Soldering Heat Test Conditions

温度: 270±5℃ 时间: 10±1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

包装形式 / BULK

Package Type	Units					Dimension (unit mm ³)		
	Units/Bag	Bags/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Bag	Inner Box	Outer Box
TO-220/F	200	10	2,000	5	10,000	135×190	237×172×102	560×245×195